

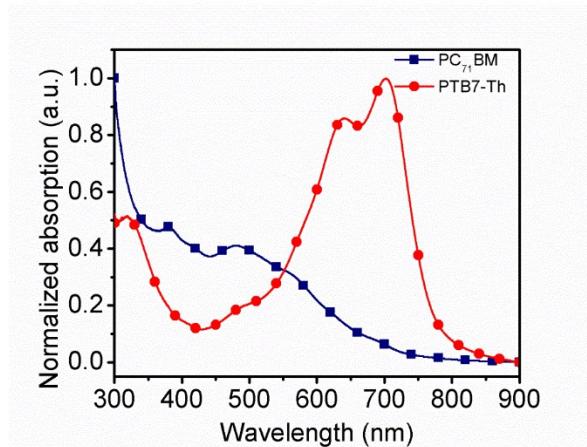
## Supporting Information

### High Performance Opaque and Semitransparent Organic Solar Cells with Good Tolerance to Film Thickness Realized by a Unique Solid Additives

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**Figure S1.** Normalized absorption spectra of PTB7-Th and PC<sub>71</sub>BM

**Table S1.** Photovoltaic parameters of control OSCs with different active layer thickness

Thickness (nm)	V <sub>oc</sub> (V)	J <sub>sc</sub> (mA/cm <sup>2</sup> )	FF (%)	PCE (max) <sup>b</sup> (%)
300	0.766	14.21	50.71	5.52 (5.79)
200	0.775	18.92	59.76	8.87 (9.14)
120	0.783	18.26	65.49	9.26 (9.44)
60	0.796	13.38	68.16	7.25 (7.53)

<sup>b</sup> Statistical data obtained from 10 devices;

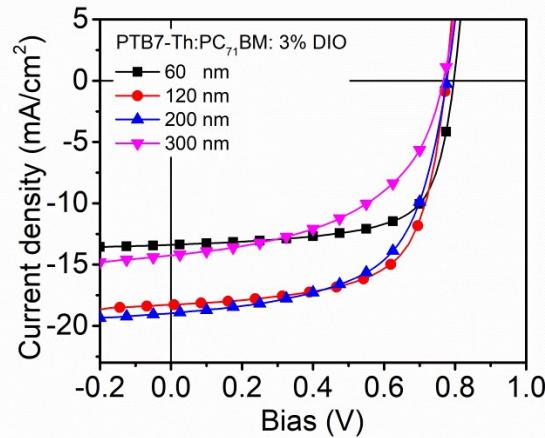
**Table S2.** Photovoltaic parameters of OSCs with different active areas

Device	Area (mm <sup>2</sup> ) <sup>c</sup>	V <sub>oc</sub> (V)	J <sub>sc</sub> (mA/cm <sup>2</sup> )	FF (%)	PCE (max) (%)
Control <sup>a</sup>	2.3	0.783	18.26	65.49	9.26 (9.44)
	11.0	0.782	18.36	63.86	9.16 (9.28)
Optimized <sup>b</sup>	2.3	0.806	20.05	71.30	11.52 (11.64)
	11.0	0.807	20.14	66.99	10.89 (11.15)

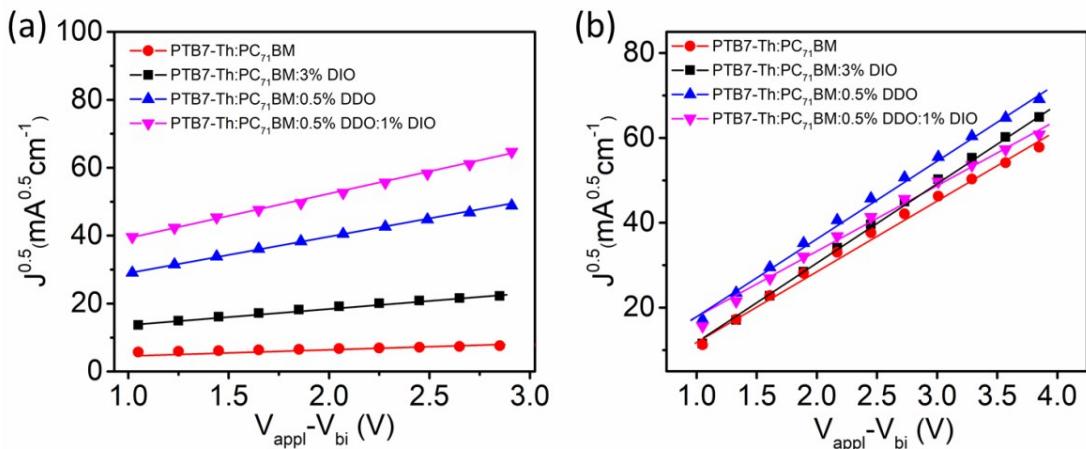
<sup>a</sup> Device structure: ITO/ZnO/PTB7-Th:PC<sub>71</sub>BM:3%DIO/MoO<sub>3</sub>/Ag;

<sup>b</sup> Device structure: ITO/ZnO/PTB7-Th:PC<sub>71</sub>BM:0.5%DDO: 1%DIO/MoO<sub>3</sub>/Ag;

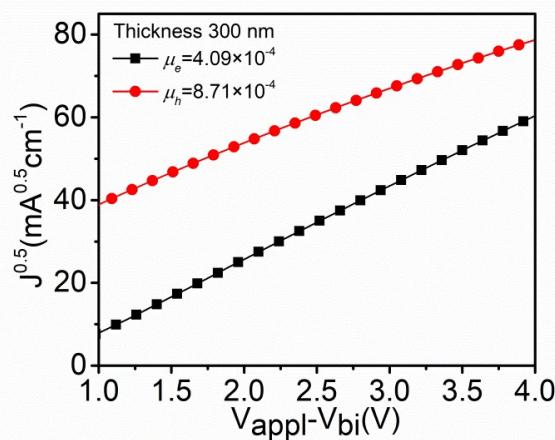
<sup>c</sup> the effective device area, device performance of 11.0 mm<sup>2</sup> obtained from 10 devices;



**Figure S2.** J-V curves of control device with different active layer thickness



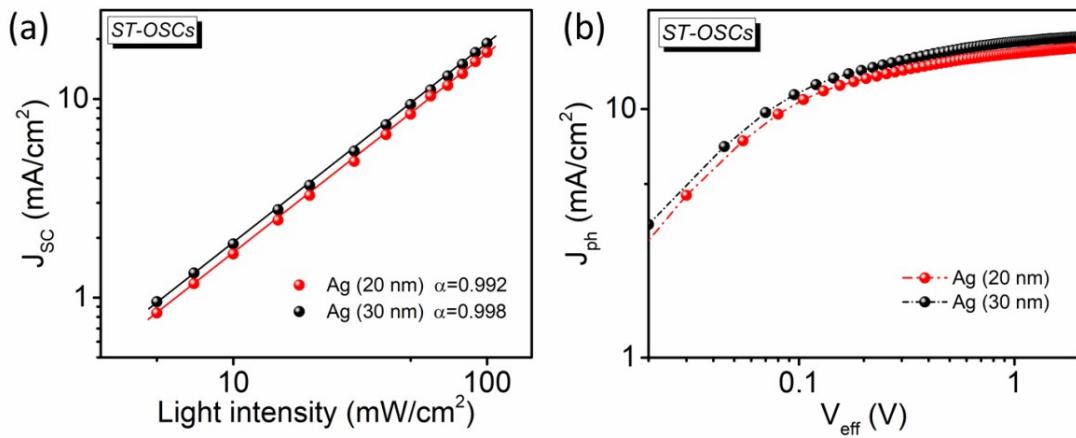
**Figure S3.** Fitting curves of hole (a) and electron (b) mobility of PTB7-Th: PC<sub>71</sub>BM, PTB7-Th: PC<sub>71</sub>BM: 3%DIO, PTB7-Th: PC<sub>71</sub>BM: 0.5%DDO and PTB7-Th: PC<sub>71</sub>BM: 0.5%DDO: 1%DIO films



**Figure S4.** Fitting curves of hole and electron mobility of PTB7-Th: PC<sub>71</sub>BM: 0.5%DDO: 1%DIO film with 300 nm thickness

**Table S3.** Charge mobilities and balance factor of DDO contained and control devices in this work

DDO	DIO	$\mu_h$ ( $\text{cm}^2 \text{V}^{-1}\text{S}^{-1}$ )	$\mu_e$ ( $\text{cm}^2 \text{V}^{-1}\text{S}^{-1}$ )	$\mu_h/\mu_e$
w/o	w/o	$2.18 \times 10^{-5}$	$4.34 \times 10^{-6}$	5.02
w/o	3% DIO	$5.42 \times 10^{-4}$	$3.05 \times 10^{-4}$	1.78
0.5% DDO	w/o	$1.12 \times 10^{-3}$	$9.56 \times 10^{-4}$	1.17
0.5% DDO	1% DIO	$1.24 \times 10^{-3}$	$1.05 \times 10^{-3}$	1.18



**Figure S5.** (a) Dependence of  $J_{SC}$  on light intensity ( $100 \text{ mW}/\text{cm}^2$  to  $5 \text{ mW}/\text{cm}^2$ ) and (b) photocurrent versus effective voltage of ST-OSCs with different Ag thickness